

<b>PCN Number:</b>	20221013001.2	<b>PCN Date:</b>	October 14, 2022
<b>Title:</b>	Qualification of new Fab site (DMOS6) using qualified Process Technology, Die Revision, and additional BOM option for select devices		
<b>Customer Contact:</b>	<a href="#">PCN Manager</a>	<b>Dept:</b>	Quality Services
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Apr 12, 2023	<b>Sample requests accepted until:</b>	Nov 14, 2022*

**\*Sample requests received after Oct 14, 2022 will not be supported.**

**Change Type:**

<input type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Assembly Materials
<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process
<input checked="" type="checkbox"/>	Wafer Fab Site	<input checked="" type="checkbox"/>	Wafer Fab Materials	<input checked="" type="checkbox"/>	Wafer Fab Process
		<input type="checkbox"/>	Part number change		

**PCN Details**

**Description of Change:**

Texas Instruments is pleased to announce the qualification of a new fab & process technology (DMOS6, LBC9) and BOM option for selected devices as listed below in the product affected section. Construction differences are noted below:

Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
DL-LIN	PRISM	200 mm	DMOS6	LBC9	300 mm

The die was also changed as a result of the process change.

Additionally, there will be a BOM/Assembly options introduced for these devices:

**Group 1 (DW20) BOM options**

	Current	Additional
Bond wire composition, Diameter	Au, 1.15 mils	Cu, 0.96 mil
Mount Compound	4042500	4147858
Mold Compound	4205694	4211880
Probe Site	Not in Process flow	CDPR

**Group 2 (DW24) BOM options**

	Current	Additional
Bond wire composition, Diameter	Au, 1.15 mils	Cu, 0.96 mil
Probe Site	Not in Process flow	CDPR

Tube and some G4 versions of the devices are included in EOL notice PDN# 20221013002.3

**Reason for Change:**

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

**Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):**

None

**Impact on Environmental Ratings**

Checked boxes indicate the status of environmental ratings following implementation of this

change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change

**Changes to product identification resulting from this PCN:**

**Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	DLN	USA	Dallas
<b>DMOS6</b>	<b>DM6</b>	<b>USA</b>	<b>Dallas</b>

**Die Rev:**

Current	New
Die Rev [2P] A,B,C	Die Rev [2P] <b>A</b>

Sample product shipping label (not actual product label)

**TEXAS INSTRUMENTS**  
 MADE IN: Malaysia  
 2DC: 2Q:  
 MSL 2 /260C/1 YEAR SEAL DT  
 MSL 1 /235C/UNLIM 03/29/04  
 OPT:  
 ITEM: 39  
**LBL: 5A (L)T0:1750**

(1P) SN74LS07NSR  
 (Q) 2000 (D) 0336  
 (31T) LOT: 3959047MLA  
 (4W) TKY (1T) 7523483SI2  
 (P)  
 (2P) REV: (V) 0033317  
 (20L) GSO: SHE (21L) CCO: USA  
 (22L) ASO: MLA (23L) ACO: MYS

**Product Affected:**

**Group 1 Device list (DW20)**

TPIC6595DWR	TPIC6596DWRG4	TPIC6B595DWR	TPIC6B596DWR
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**Group 2 Device list (DW24)**

TPIC6A595DWR	TPIC6A596DWRG4
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For alternate parts with similar or improved performance, please visit the product page on [ti.com](http://ti.com).

## Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### TPIC6x59xDW Qualification Approved 16-Sept-2022

#### Product Attributes

Attributes	Qual Device: TPIC6595DWR	Qual Device: TPIC6A595DWR	Qual Device: TPIC6596DWRG4	Qual Device: TPIC6B595DWR	Qual Device: TPIC6B596DWR	Qual Device: TPIC6A596DWRG4	QBS Process Reference: LMR33630CQRNXRQ1	QBS Package Reference: AMC1305M25QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40C to 125C	-40C to 125C	-40C to 125C	-40C to 125C	-40C to 125C	-40C to 125C	-40C to 125C	-40 to +125 C
Product Function	Power Management	Power Management	Power Management	Power Management	Power Management	Power Management	Power Management	Signal Chain
Wafer Fab Supplier	DMOS6	DMOS6	DMOS6	DMOS6	DMOS6	DMOS6	DMOS6	AIZU, DMOS5
Die Revision	A0	A0	A0	A0	A0	A0	B	C, F
Assembly Site	TAI	TAI	TAI	TAI	TAI	TAI	CDAT	TAI
Package Type	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	VQFN-HR	SOIC
Package Designator	DW	DW	DW	DW	DW	DW	RNX	DW
Ball/Lead Count	20	24	20	20	20	24	12	16

- QBS: Qual By Similarity
- Qual Device TPIC6595DWR is qualified at MSL1 260C
- Qual Device TPIC6A595DWR is qualified at MSL1 260C
- Qual Device TPIC6596DWRG4 is qualified at MSL1 260C
- Qual Device TPIC6B595DWR is qualified at MSL1 260C
- Qual Device TPIC6B596DWR is qualified at MSL1 260C
- Qual Device TPIC6A596DWRG4 is qualified at MSL1 260C

#### Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: TPIC6595DWR	Qual Device: TPIC6A595DWR	Qual Device: TPIC6596DWRG4	Qual Device: TPIC6B595DWR	Qual Device: TPIC6B596DWR	Qual Device: TPIC6A596DWRG4	QBS Process Reference: LMR33630CQRNXRQ1	QBS Package Reference: AMC1305M25QDWRQ1
Test Group A -- Accelerated Environment Stress Tests														
PC	A1	JEDEC J-STD-020 JESD22-A113	3	231	Automotive Preconditioning	Level 1-260C	-	-	-	-	-	Pass	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	231	Automotive Preconditioning	Level 2-260C	-	-	-	-	-	-	Pass	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	231	Automotive Preconditioning	Level 3-260C	-	-	-	-	-	-	-	Pass
bHAST	A2	JEDEC JESD22-A101	3	77	Biased HAST, 130C/85%RH	96 Hours	-	-	-	-	-	3/231/0	-	3/231/0
bHAST	A2	JEDEC JESD22-A101	3	77	Biased HAST, 110C/85%RH	264 Hours	-	-	-	-	-	-	3/231/0	-
uHAST	A3	JEDEC JESD22-A102	3	77	Unbiased HAST, 130C/85%RH	96 Hours	-	-	-	-	-	3/231/0	-	-
uHAST	A3	JEDEC JESD22-A102	3	77	Unbiased HAST, 110C/85%RH	264 Hours	-	-	-	-	-	-	3/231/0	-
AC		JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	-	-	-	-	-	-	-	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -05/150C	500 Cycles	-	-	-	-	-	3/231/0	3/231/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	46	Power Temperature Cycle	1000 Cycles	-	-	-	-	-	1/45/0	-	-
HTSL	A6	JEDEC JESD22-A103	1	46	High Temp. Storage Life, 150C	1000 Hours	-	-	-	-	-	3/135/0	3/135/0	1/45/0

Test Group B – Accelerated Lifetime Simulation Tests														
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	-	-	-	-	-	3/231/0	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	-	-	-	-	-	3/2400/0	-
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	10000 Cycles	-	-	-	-	-	-	3/231/0	-
Test Group C – Package Assembly Integrity Tests														
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	-	-	-	-	-	1/30/0	N/A	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	-	-	-	-	-	1/30/0	N/A	3/90/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability >95% Lead Coverage	15	-	-	-	-	-	-	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	30 units	-	-	-	-	-	3/90/0	3/90/0	-
SBS	C5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	-	-	-	-	-	N/A	N/A	N/A
LI	C6	JEDEC JESD22-B105	1	50	Lead Integrity	Leads	-	-	-	-	-	N/A	N/A	N/A
Test Group D – Die Fabrication Reliability Tests														
EM	D1	JESD01	-	-	Electromigration	--	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	--	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD00 & 28	-	-	Hot Injection Carrier	--	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	--	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	--	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E – Electrical Verification Tests														
HBM	E2	AEC Q100-002	1	3	ESD - HBM	2500 V	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-up	+100mA, 150C	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0	-
ED	E5	AEC Q100-005	3	30	Electrical Distribution	Cpk > 1.67	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	3/30/0	3/30/0	3/30/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable  
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours  
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours  
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles  
Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>  
Green/Pb-free Status:  
Qualified Pb-Free(SMT) and Green

TI Qualification ID: R-NPD-2202-065



TI Information  
Select Disclosure

### Automotive Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### LBC9 MetDCU with 1.0 mil Cu wire in TITL SOIC PKG Approved 13-Sept-2022

#### Product Attributes

Attributes	Qual Device:
Automotive Grade Level	TPIC6A596DWRG4
Operating Temp Range	Grade 1
Product Function	-40 to +125 C
Wafer Fab Supplier	Power Management
Die Revision	DMOS6
Assembly Site	A0
Package Type	TAI
Package Designator	SOIC
Ball/Lead Count	DW
	24

- QBS: Qual By Similarity  
- Qual Device TPS22919QDCKRQ1 is qualified at LEVEL1-260C

**Qualification Results**  
**Data Displayed as: Number of lots / Total sample size / Total failed**

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: TPIC6A596DWRG4
<b>Test Group A – Accelerated Environment Stress Tests</b>							
PC	A1	-	3	22	SAM Analysis, Pre Stress	Completed	3/66/0
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 2-260C	No fails
PC	A1	-	3	22	SAM Analysis, Post Stress	Completed	3/66/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0
HAST	A2	-	3	1	Cross Section, Post bHAST 96 Hours	Completed	3/3/0
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 96 Hours	Wires	3/90/0
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	3/90/0
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	3/90/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	192 Hours	3/210/0
HAST	A2	-	3	1	Cross Section, Post bHAST 192 Hours	Completed	3/3/0
HAST	A2	-	3	22	SAM Analysis, Post bHAST, 192 Hours	Completed	3/66/0
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 192 Hours	Wires	3/90/0
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	3/90/0
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	3/90/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
TC	A4	-	3	1	Cross Section, Post T/C 500 Cycles	Completed	3/3/0
TC	A4	-	3	22	SAM Analysis, Post T/C, 500 Cycles	Completed	3/66/0
TC	A4	-	3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	3/90/0
TC	A4	-	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	3/90/0
TC	A4	-	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	3/90/0

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: TPIC6A596DWRG4
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	1000 Cycles	3/210/0
TC	A4	-	3	1	Cross Section, Post T/C 1000 Cycles	Completed	3/3/0
TC	A4	-	3	22	SAM Analysis, Post T/C, 1000 Cycles	Completed	3/66/0
TC	A4	-	3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/90/0
TC	A4	-	3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/90/0
TC	A4	-	3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/90/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle -40/125C	1000 Cycles	1/45/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle -40/125C	2000 Cycles	1/45/0
HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	3/135/0
HTSL	A6	-	3	1	Cross Section, Post HTSL 1000 Hours	Completed	3/3/0
HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	3/132/0
HTSL	A6	-	3	1	Cross Section, Post HTSL 2000 Hours	Completed	3/3/0

Test Group C – Package Assembly Integrity Tests							
WBS	C1	AEC Q100-001	3	30	Wire Bond Shear, Cpk>1.67	Wires	3/30/0
WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull over Ball, Cpk >1.67	Wires	3/30/0

**A1 (PC): Preconditioning:**

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

**Ambient Operating Temperature by Automotive Grade Level:**

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C

Grade 3 (or I): -40°C to +85°C

**E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):**

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

**Green/Pb-free Status:**

Qualified Pb-Free(SMT) and Green

TI Qualification ID: R-NPD-2209-054

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	<a href="mailto:PCN_ww_admin_team@list.ti.com">PCN_ww_admin_team@list.ti.com</a>

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